October 2014

FDMS7680

N-Channel PowerTrench® MOSFET
30 V, 6.9 mΩ

Features

- Max $r_{DS(on)}$ = 6.9 mΩ at V_{GS} = 10 V, I_D = 14 A
- Max $r_{DS(on)}$ = 11 mΩ at V_{GS} = 4.5 V, I_D = 11 A
- Advanced Package and Silicon combination for low $r_{DS(on)}$ and high efficiency
- Next generation enhanced body diode technology, engineered for soft recovery.
- MSL1 robust package design
- 100% UIL tested
- RoHS Compliant

General Description

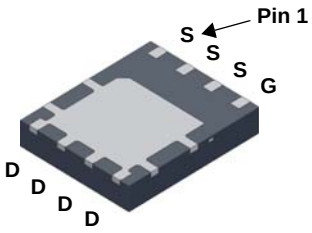
This N-Channel MOSFET has been designed specifically to improve the overall efficiency and to minimize switch node ringing of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $r_{DS(on)}$, fast switching speed and body diode reverse recovery performance.

Applications

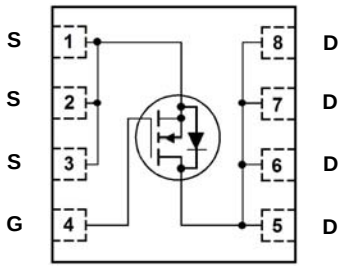
- IMVP Vcore Switching for Notebook
- VRM Vcore Switching for Desktop and Server
- OringFET / Load Switch
- DC-DC Conversion

Top

Bottom



Power 56



MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			30	V
V_{GS}	Gate to Source Voltage			+/-20	V
I_D	Drain Current -Continuous (Package limited)	T_C = 25 °C		28	A
	-Continuous (Silicon limited)	T_C = 25 °C		53	
	-Continuous	T_A = 25 °C	(Note 1a)	14	
	-Pulsed		(Note 4)	80	
E_{AS}	Single Pulse Avalanche Energy		(Note 3)	29	mJ
P_D	Power Dissipation	T_C = 25 °C		33	W
	Power Dissipation	T_A = 25 °C	(Note 1a)	2.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.7	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

Package Marking and Ordering Information

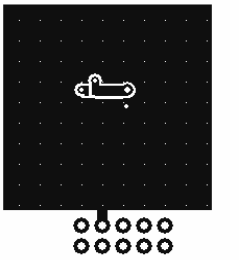
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS7680	FDMS7680	Power 56	13 ”	12 mm	3000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted

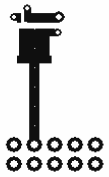
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		13		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate to Source Leakage Current, Forward	V_{GS} = 20 V, V_{DS} = 0 V			100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	1.25	1.9	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		-6		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V , I_D = 14 A		5.6	6.9	mΩ
		V_{GS} = 4.5 V, I_D = 11 A		8.0	11	
		V_{GS} = 10 V, I_D = 14 A, T_J = 125 °C		7.3	10.1	
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 14 A		85		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz		1390	1850	pF
C_{oss}	Output Capacitance			430	575	pF
C_{rss}	Reverse Transfer Capacitance			60	85	pF
R_g	Gate Resistance		0.1	0.9	2.0	Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 15 V, I_D = 14 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		10	20	ns
t_r	Rise Time			4	10	ns
$t_{d(off)}$	Turn-Off Delay Time			21	34	ns
t_f	Fall Time			3	10	ns
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V; V_{DD} = 15 V, I_D = 14 A		20	28	nC
Q_g	Total Gate Charge	V_{GS} = 0 V to 4.5 V; V_{DD} = 15 V, I_D = 14 A		9	13	
Q_{gs}	Gate to Source Charge	V_{DD} = 15 V, I_D = 14 A		4.6		nC
Q_{gd}	Gate to Drain “Miller” Charge			2.3		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 2.1 A (Note 2)		0.74	1.2	V
		V_{GS} = 0 V, I_S = 14 A (Note 2)		0.83	1.3	
t_{rr}	Reverse Recovery Time	I_F = 14 A, di/dt = 100 A/μs		24	39	ns
Q_{rr}	Reverse Recovery Charge			8	15	nC
t_{rr}	Reverse Recovery Time	I_F = 14 A, di/dt = 300 A/μs		20	36	ns
Q_{rr}	Reverse Recovery Charge			15	27	nC

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 50 °C/W when mounted on a 1 in^2 pad of 2 oz copper.



b. 125 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. Starting T_J = 25 °C, L = 0.3 mH, I_{AS} = 14 A, V_{DD} = 27 V, V_{GS} = 10 V.
4. Pulse Id refers to Figure.11 Forward Bias Safe Operation Area.

Typical Characteristics T_J = 25 °C unless otherwise noted

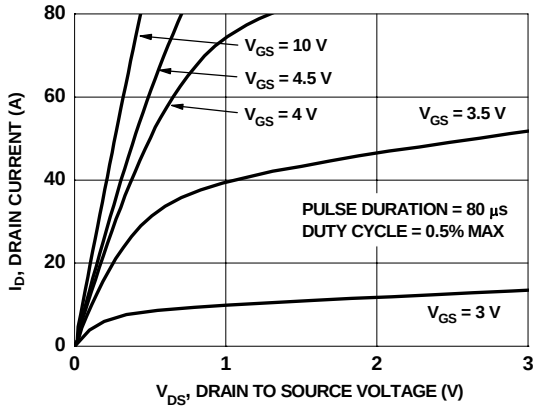


Figure 1. On Region Characteristics

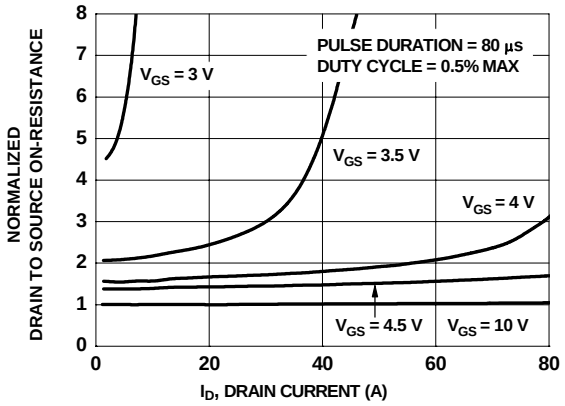


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

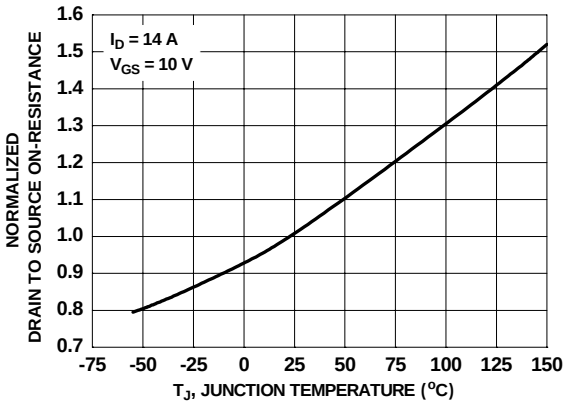


Figure 3. Normalized On Resistance vs Junction Temperature

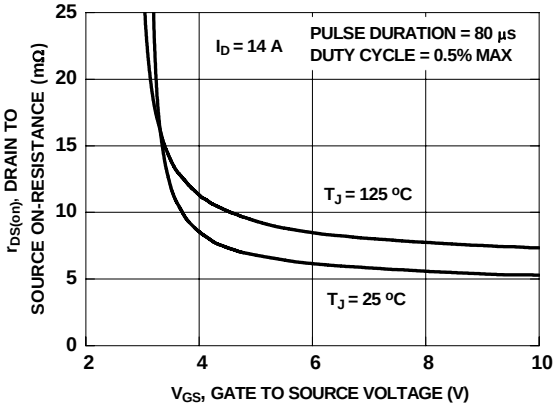


Figure 4. On-Resistance vs Gate to Source Voltage

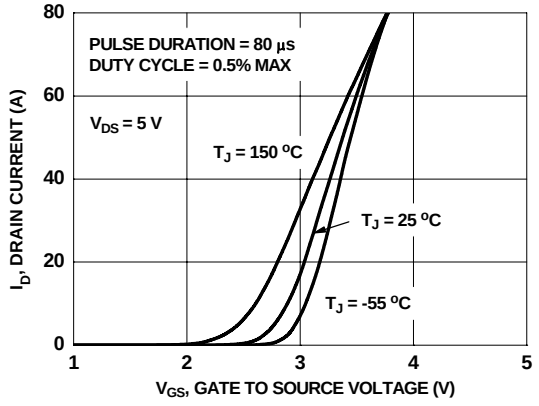


Figure 5. Transfer Characteristics

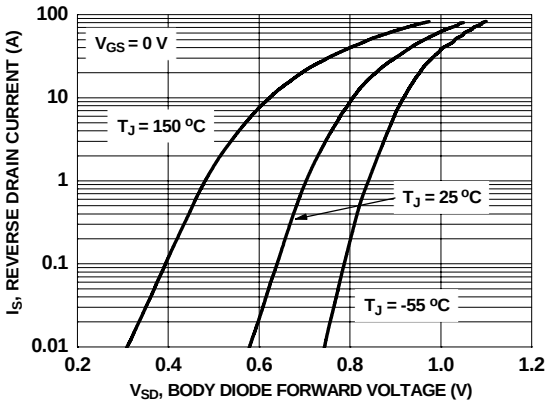


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted

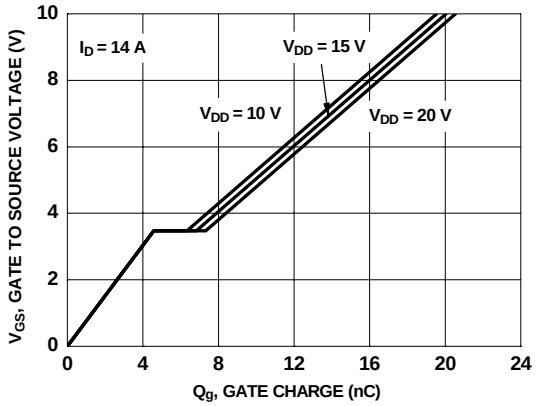


Figure 7. Gate Charge Characteristics

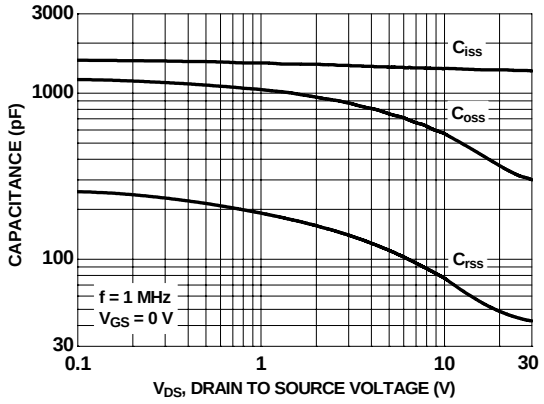


Figure 8. Capacitance vs Drain to Source Voltage

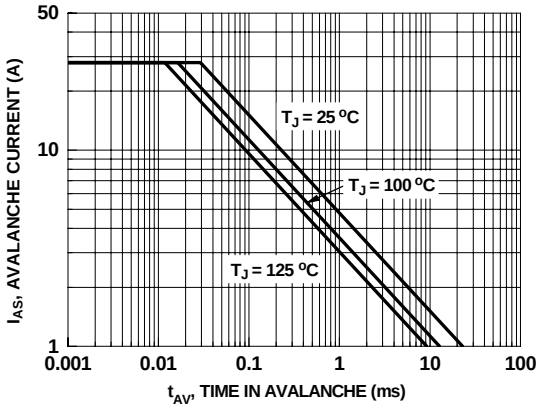


Figure 9. Unclamped Inductive Switching Capability

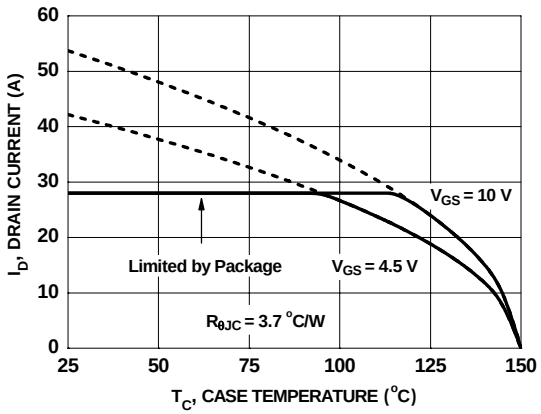


Figure 10. Maximum Continuous Drain Current vs Case Temperature

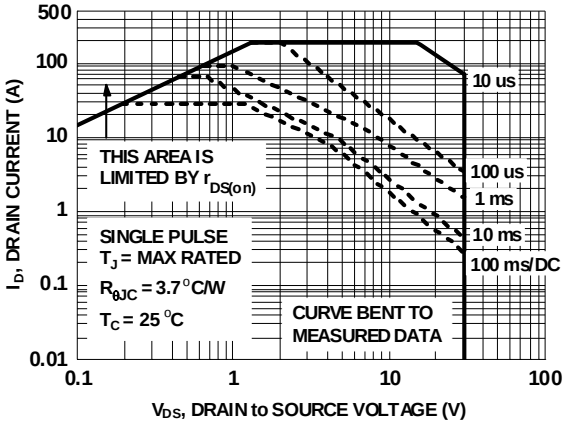


Figure 11. Forward Bias Safe Operating Area

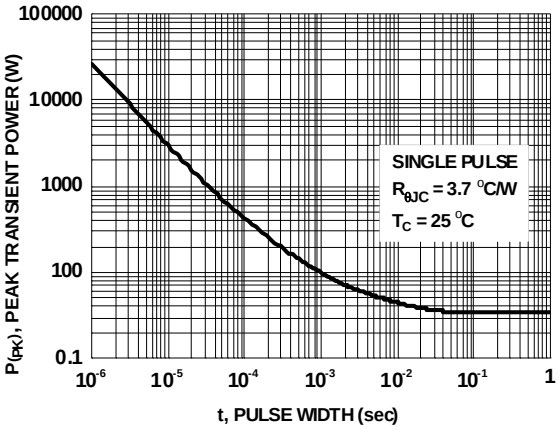


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted

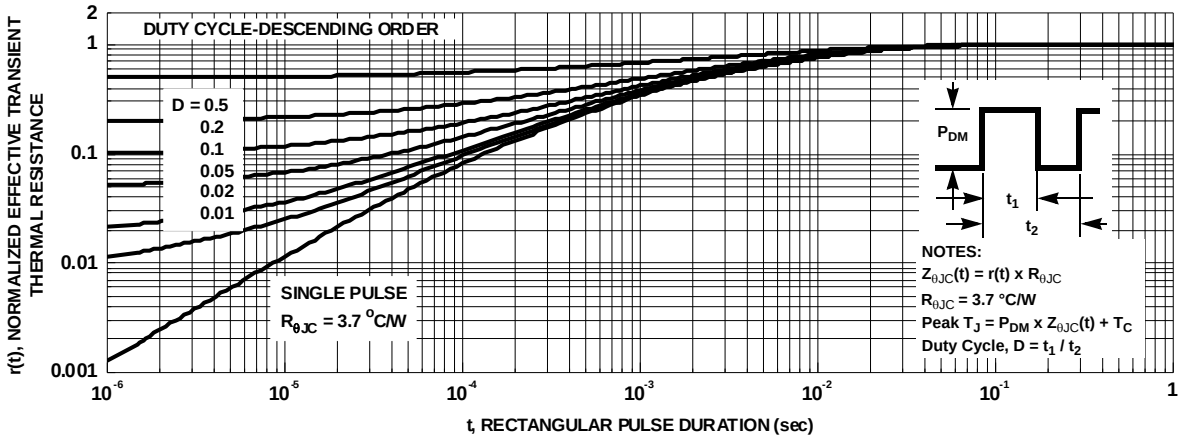


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

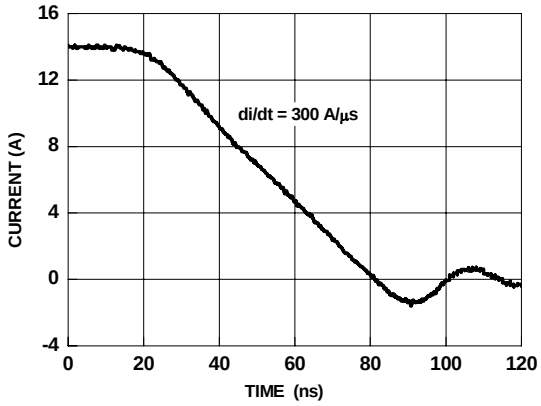
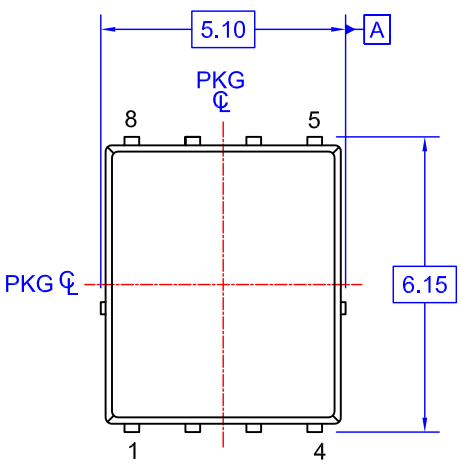
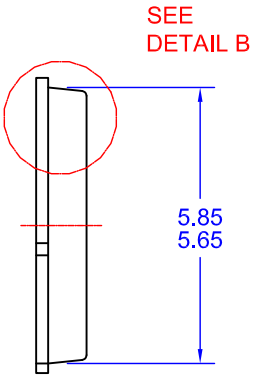
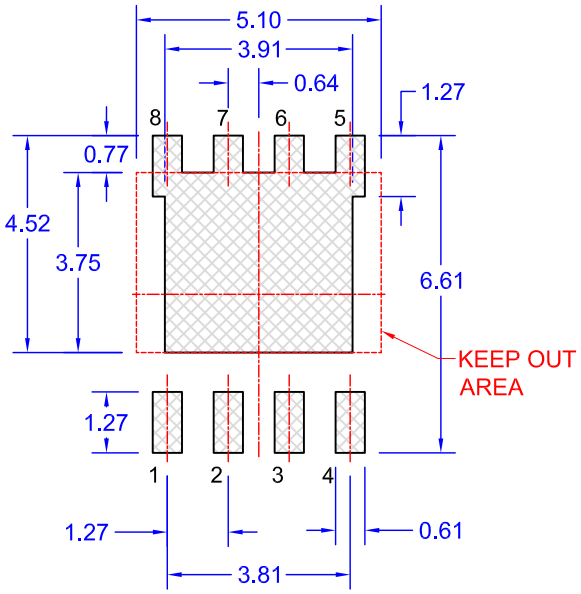


Figure 14. Body Diode Reverse Recovery Characteristics

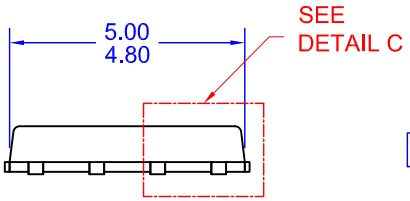


TOP VIEW

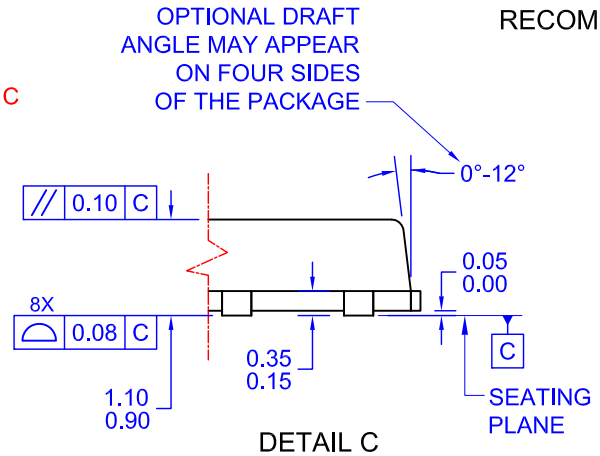




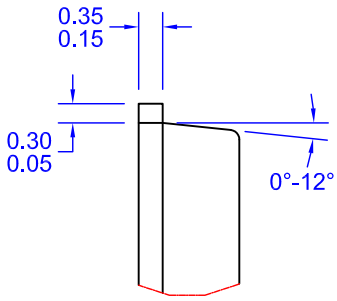
LAND PATTERN
RECOMMENDATION



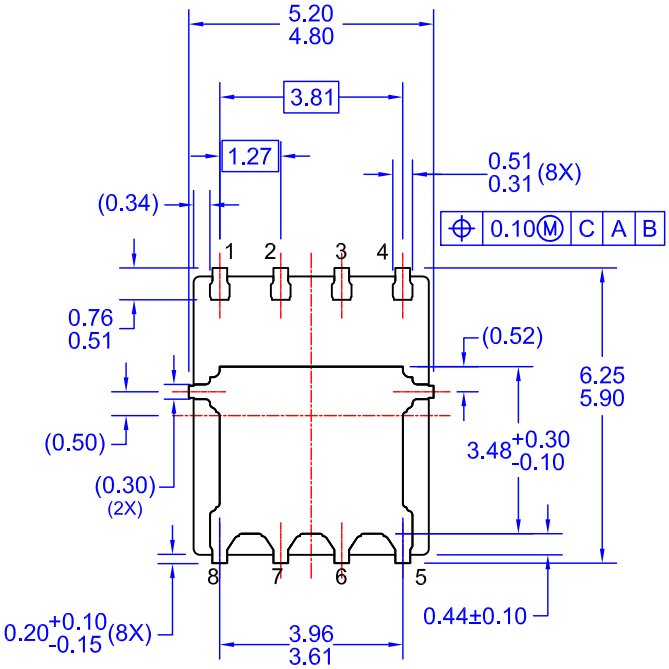
SIDE VIEW



DETAIL C
SCALE: 2:1



DETAIL B
SCALE: 2:1



BOTTOM VIEW

NOTES: UNLESS OTHERWISE SPECIFIED

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B. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
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Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

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